# SG2M023120J1J

**TriQSiC™ 1200V Silicon Carbide Power MOSFET G2**

## Features

- 
- 
- 
- 
- 
- 

## Benefits

- 
- 
- 
- 
- 




## Applications

- 
- 
- 
- 

**Table 1 Key performance and package parameters**

| Type | $V_{DS}$ | $I_{DS}$ | $R_{DS(on),\ typ}$ | $T_{J,max}$ | Marking | P |
|---|---|---|---|---|---|---|

# Table of contents


**Features** ..... 1

**Benefits** ..... 1

**Applications** ..... 1

**Table of contents** ..... 2

**1 Maximum ratings** ..... 3

**2 Thermal characteristics** ..... 3

**3 Electrical characteristics** ..... 4

**3.1 Static characteristics** ..... 4

**3.2 Dynamic characteristics** ..... 4

**3.3 Switching characteristics** ..... 5

**4 Electrical characteristic diagrams** ..... 6

**5 Package drawing ( TO-263-7L-B )** ..... 11

**6 Test conditions** ..... 12

**Revision history** ..... 13

**Attention** ..... 13

# 1 Maximum ratings

**Table 2 Maximum rating**

# SG2M023120J1J

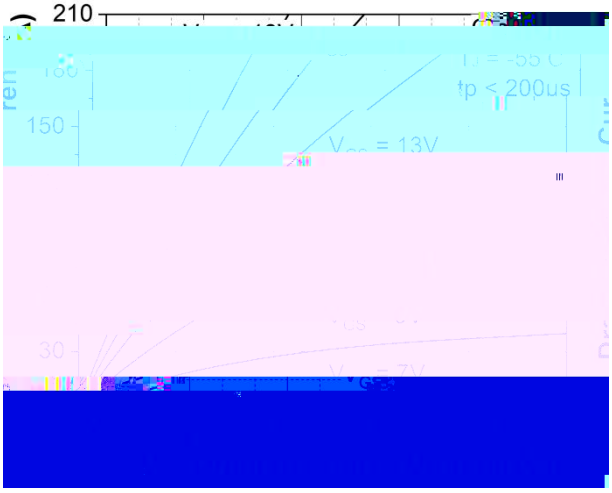
| | | | | | | | |
|---|---|---|---|---|---|---|---|
| | | | | | | | |
| | | | | | | | |
| | | | | | | | |

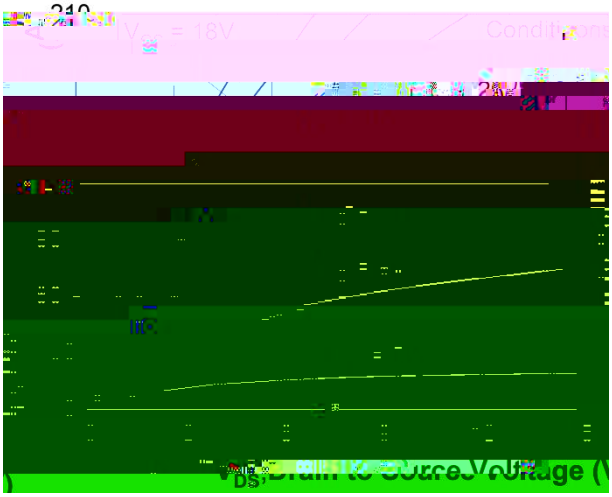
## 3.3 Switching characteristics

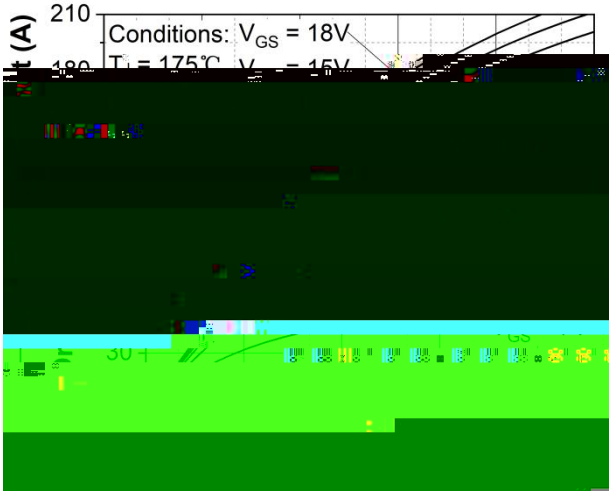
**Table 6 Dynamic characteristics**

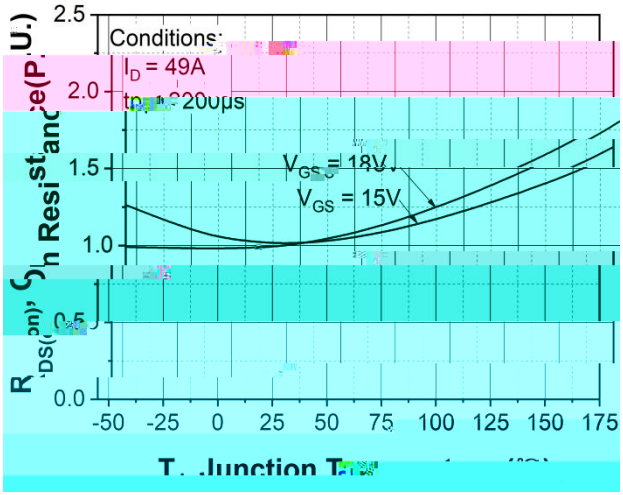
| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Conditions | Note |
|---|---|---|---|---|---|---|---|

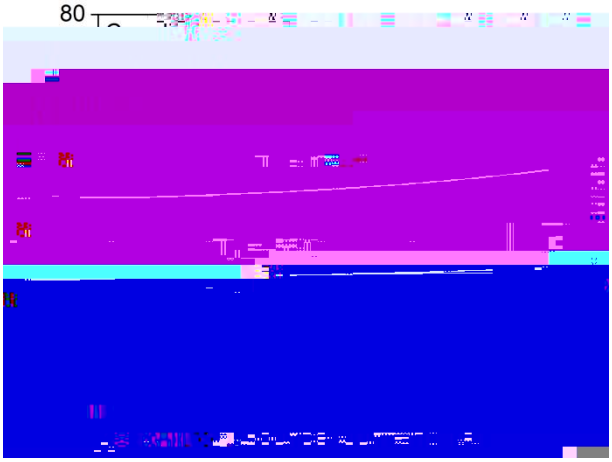
## 4 Electrical characteristic diagrams

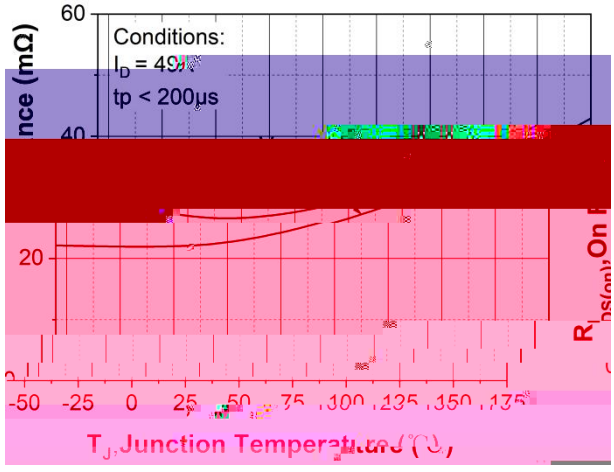


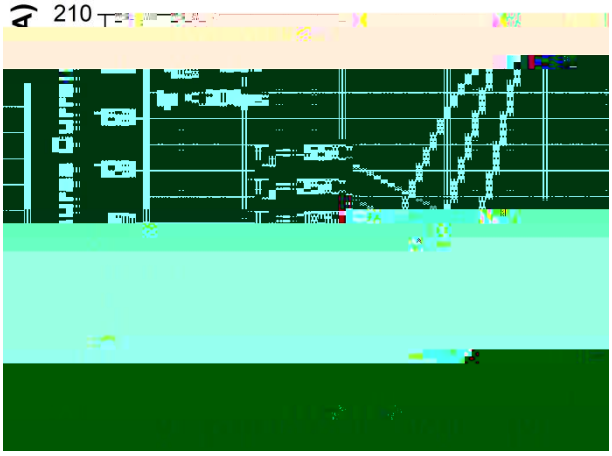



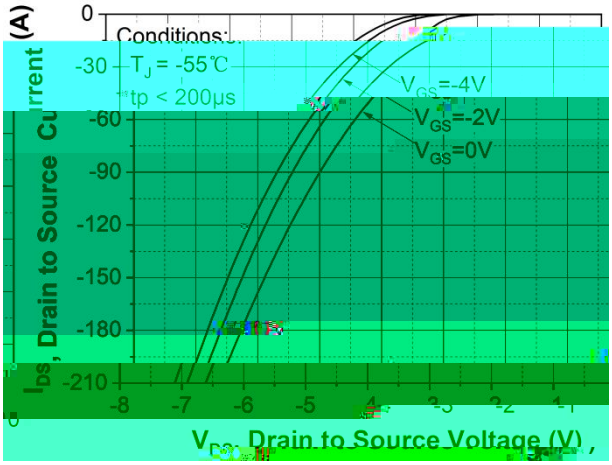



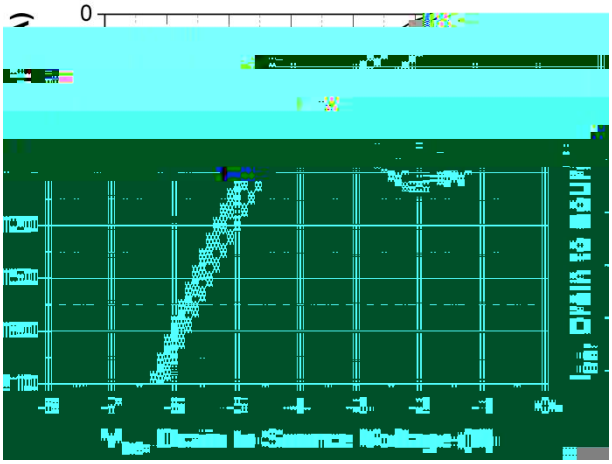



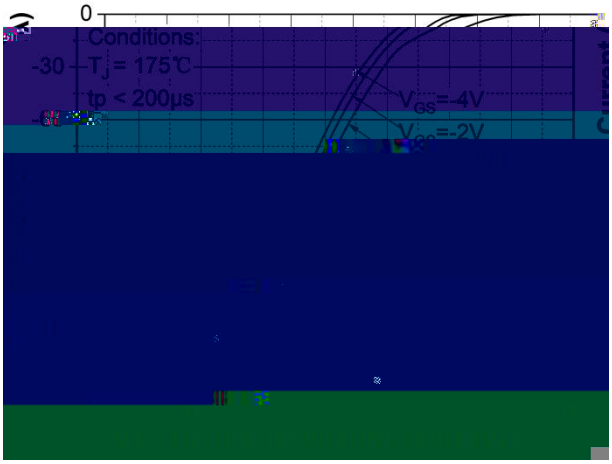



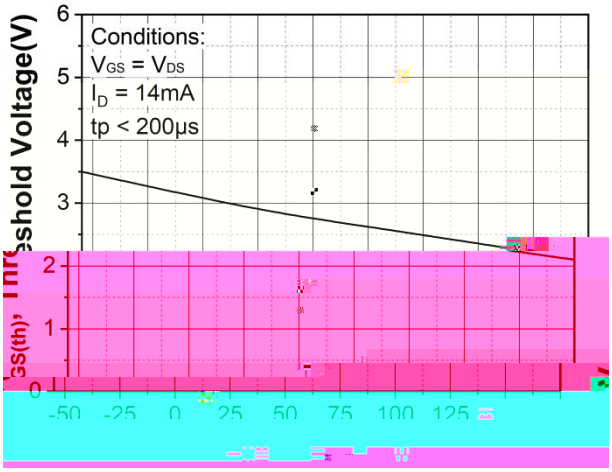
# SG2M023120J1J

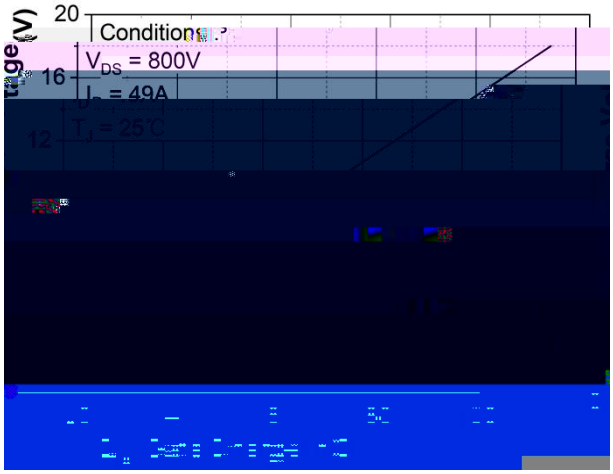






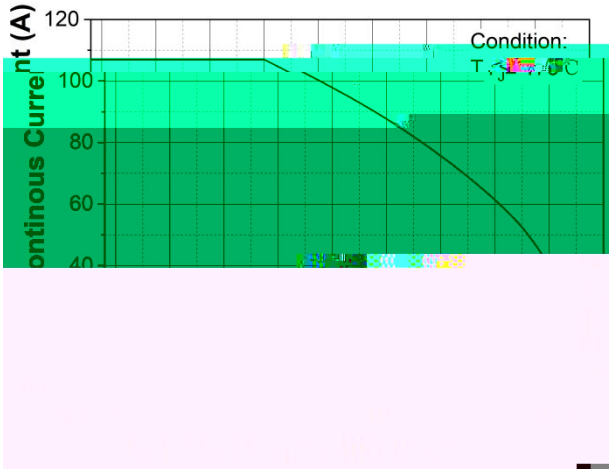



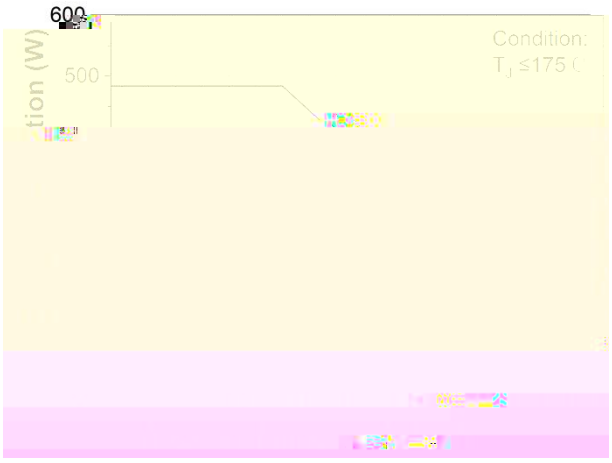



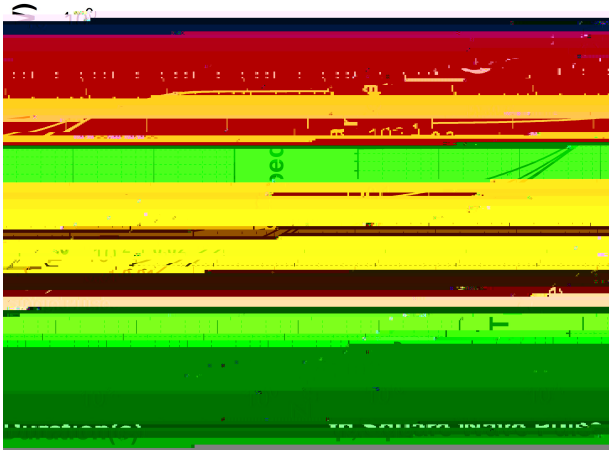
# SG2M023120J1J

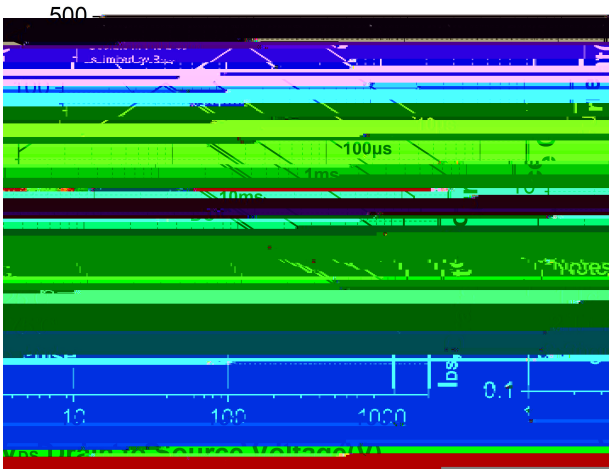
[redacted]

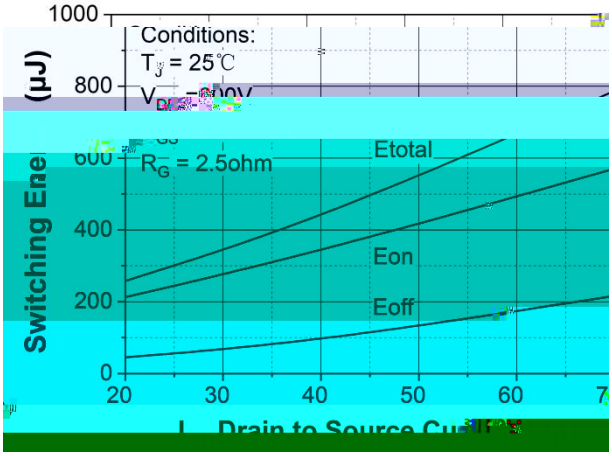
# SG2M023120J1J

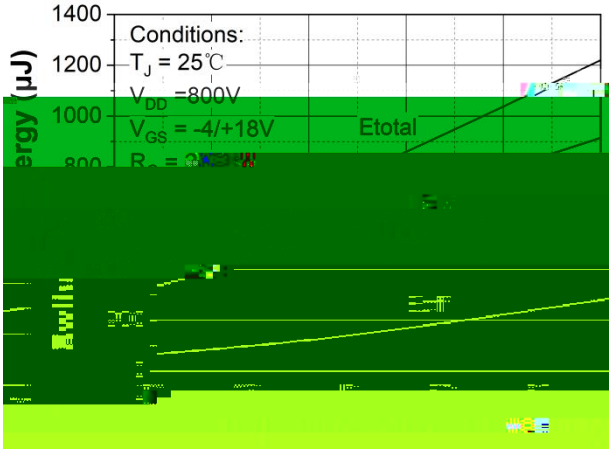


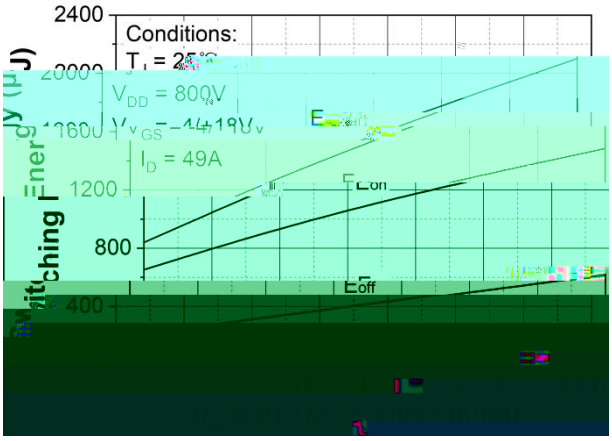



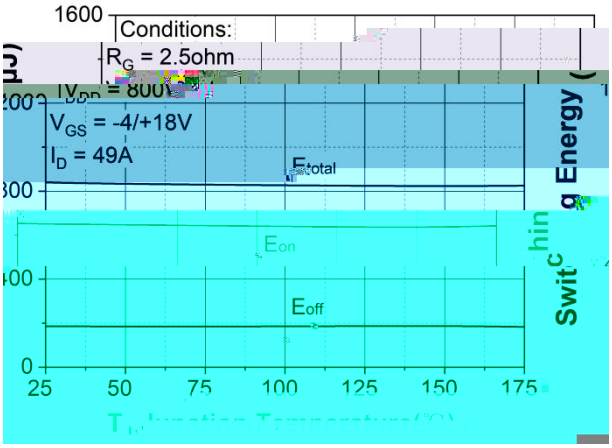


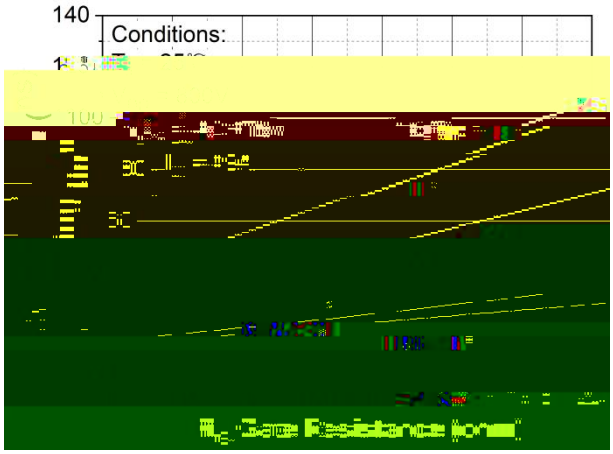



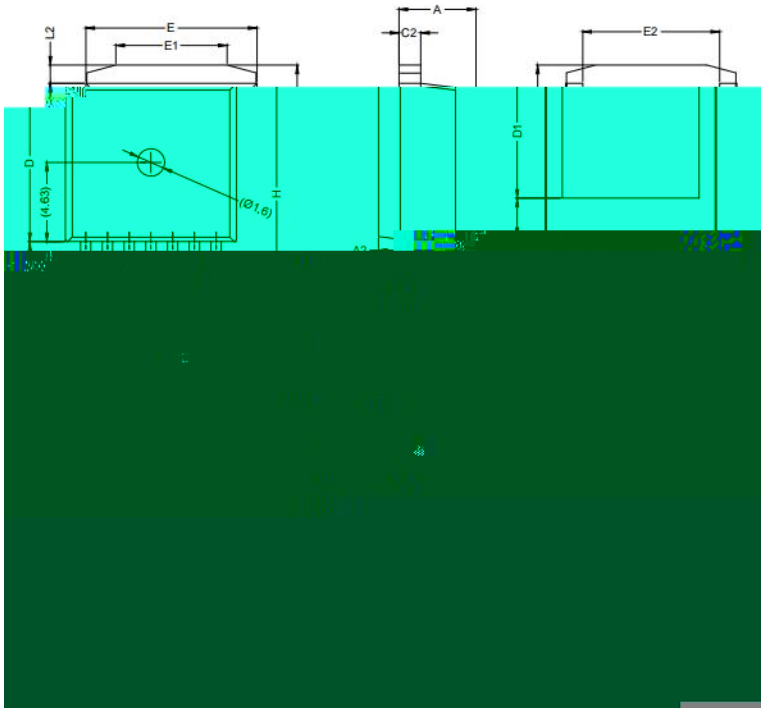
# SG2M023120J1J

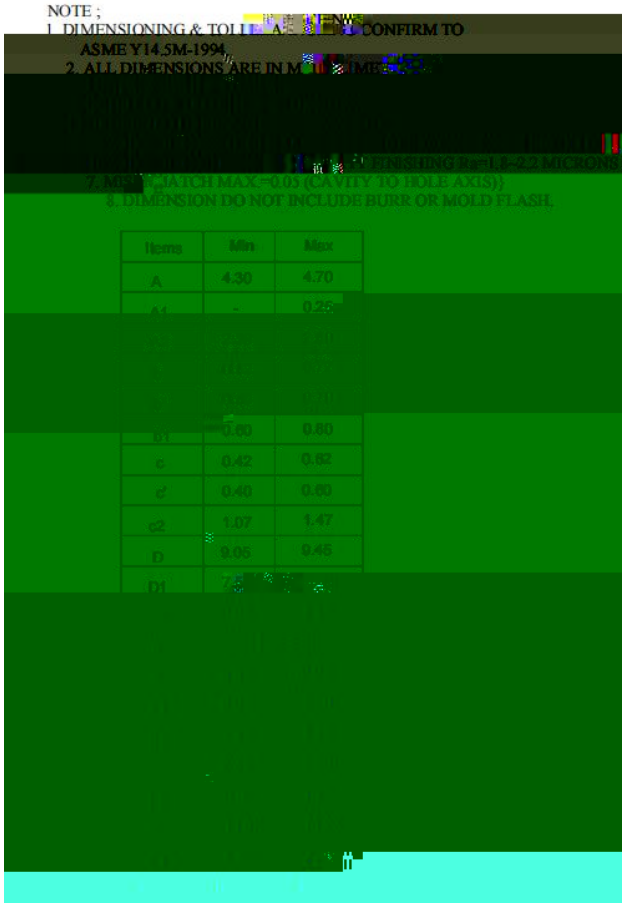


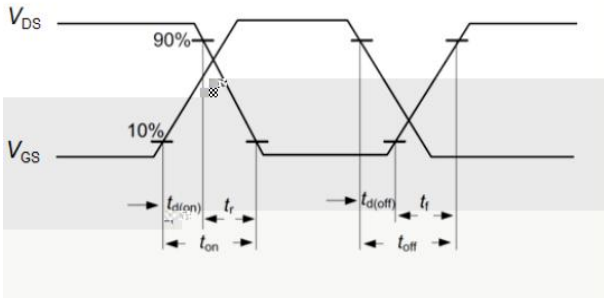



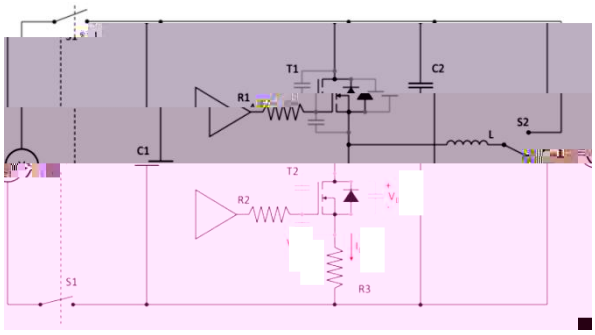
## 5 Package drawing

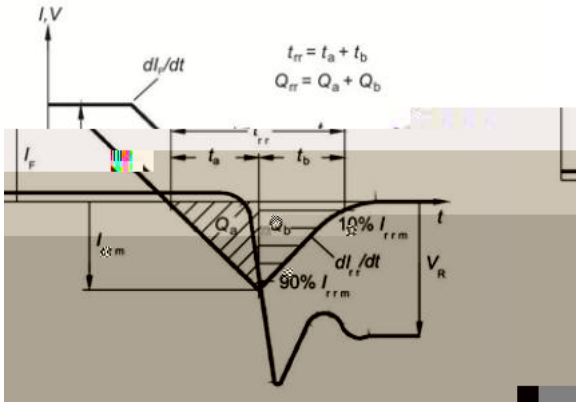


## 6 Test conditions



# SG2M023120J1J

## 1200V SiC Power MOSFET

# Revision history

**Document version**

# SG2M023120J1J